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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

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FQA32N20C

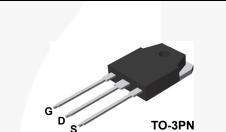
N-Channel QFET[®] MOSFET 200 V, 32 A, 82 mΩ

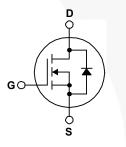
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 32 A, 200 V, $R_{DS(on)}$ = 82 m Ω (Max.) @ V_{GS} = 10 V, I_D = 16 A
- Low Gate Charge (Typ. 82.5 nC)
- Low Crss (Typ. 185 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

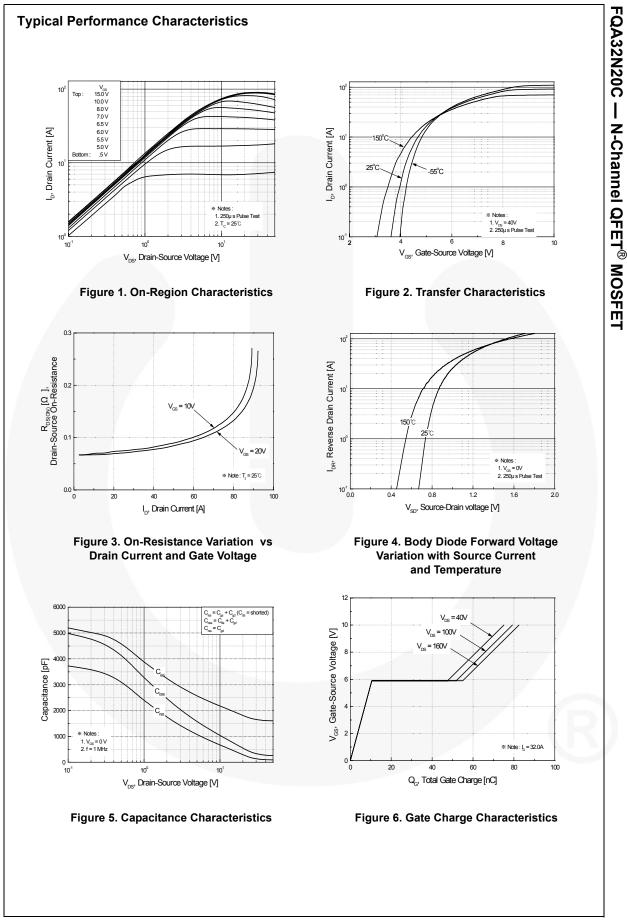
Symbol	Parameter		FQA32N20C	Unit	
V _{DSS}	Drain-Source Voltage		200	V	
I _D	Drain Current - Continuous (T _C = 25°C)		32	А	
	- Continuous (T _C = 100°C)	20.4	А	
I _{DM}	Drain Current - Pulsed	(Note 1)	128	А	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	955	mJ	
I _{AR}	Avalanche Current	(Note 1)	32	A	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	20.4	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		5.5	V/ns	
D	Power Dissipation ($T_C = 25^{\circ}C$)		204	W	
	- Derate above 25°C		1.63	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
ΤL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C	

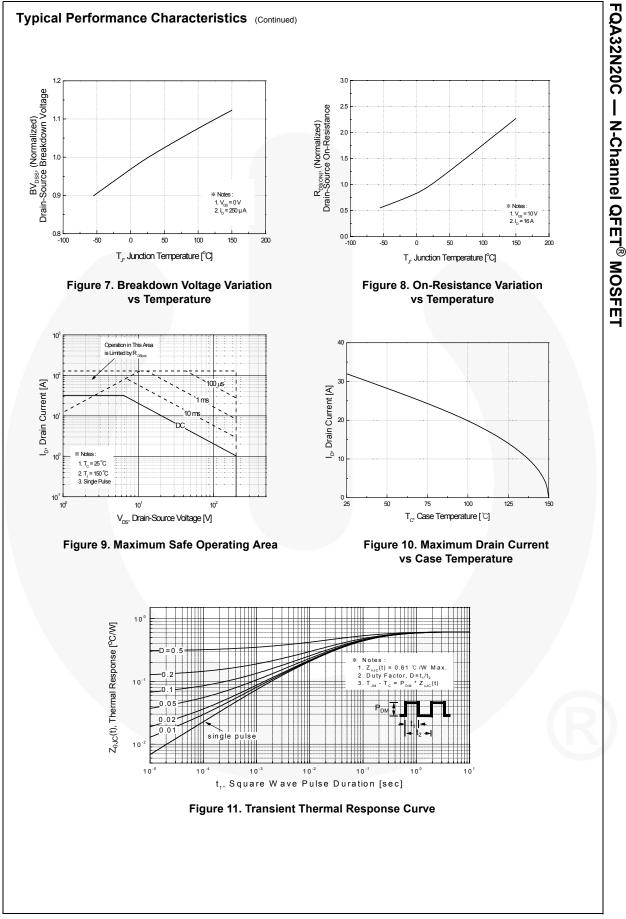
Thermal Characteristics

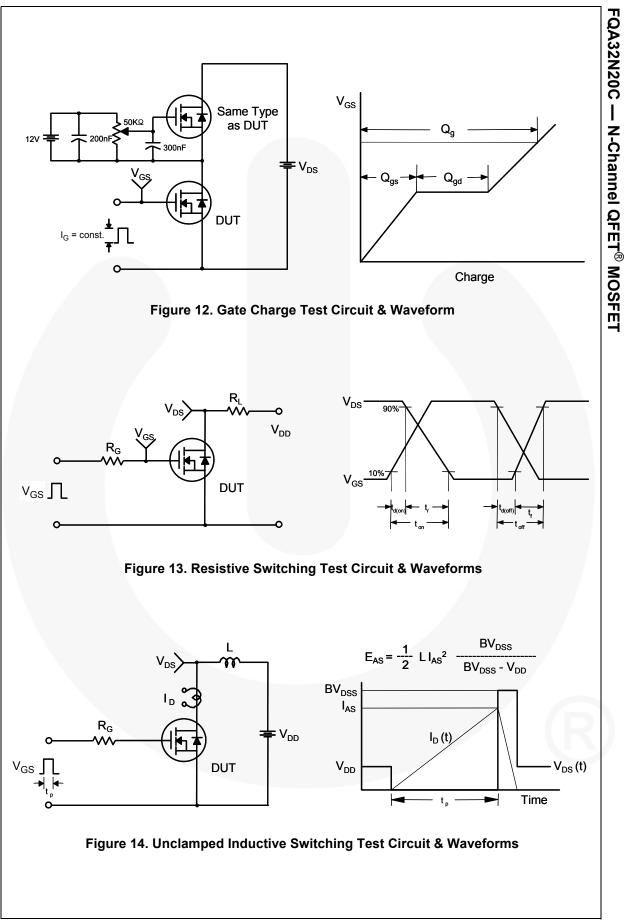
Symbol	Parameter	FQA32N20C	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.61	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W

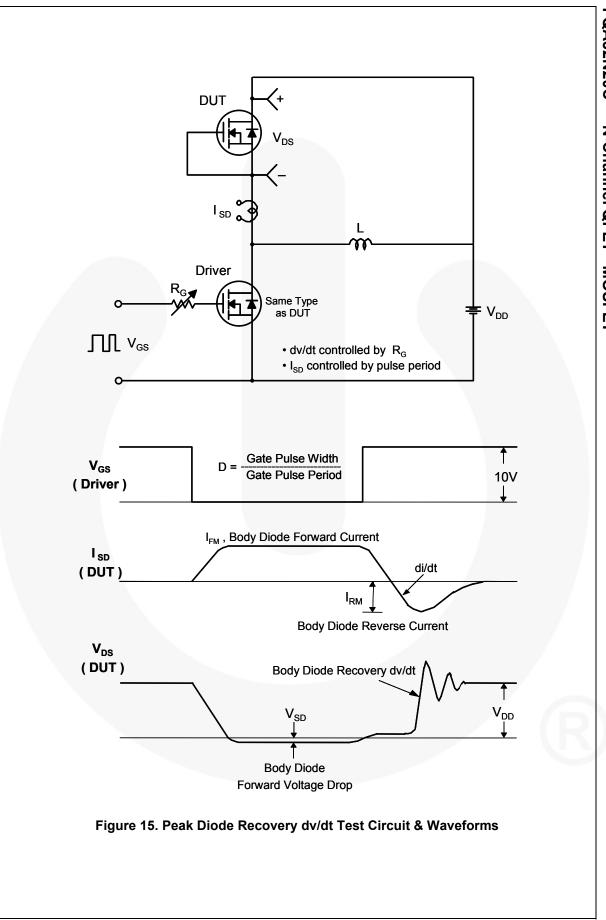
May 2014

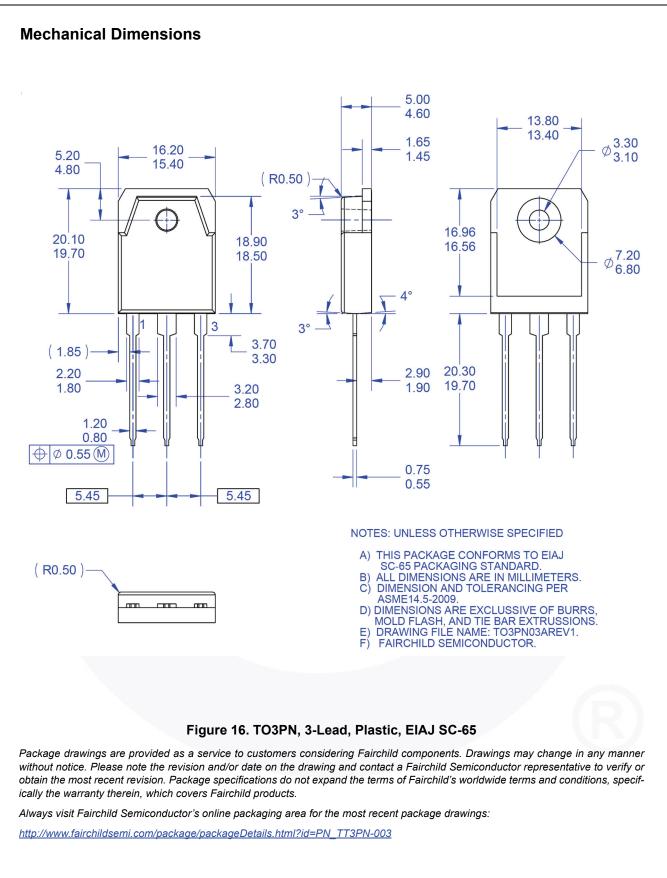
Part NumberTop MarkPackFQA32N20CFQA32N20CTO-3		Top Mark	Package Packing		Packing M	Method Reel	Reel S	Size	Tape Width		Quantity
		PN Tube		N/A	١.	N/A		30 units			
		Parameter	Γ _C = 25°C unle	ess otherv	vise noted. Test Condi	tions		Min	Тур	Мах	Unit
					iest oonur	10113		WIIII	тур	Μαλ	Unit
			taga	V=	0 V I_ = 250			200			V
V _{DSS} BV _{DSS}	Drain-Source Breakdown Voltage			V _{GS} = 0 V, I _D = 250 μA			200			V	
ΔT _J	Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current		$I_D = 250 \ \mu\text{A}$, Referenced to 25°C $V_{DS} = 200 \ \text{V}, V_{GS} = 0 \ \text{V}$				0.24		V/°C		
DSS								10	μA		
		ç		$V_{DS} = 160 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$						100	μA
SSF	Gate-Body Leakage Current, Forward			$V_{GS} = 30 V, V_{DS} = 0 V$ $V_{GS} = -30 V, V_{DS} = 0 V$						100	nA
SSSR	Gate-Bo	dy Leakage Current,	Reverse	V _{GS} =	-30 v, v _{DS} =	υv				-100	nA
)n Cha	racteris	stics									
GS(th)	-	reshold Voltage		V _{DS} =	• V _{GS} , I _D = 250) μA		2.0		4.0	V
DS(on)		ain-Source			10 V, I _D = 16 A				0.068	0.082	Ω
FS		vard Transconductance			V _{DS} = 40 V, I _D = 16 A			-	20		S
)vnam	ic Chara	acteristics									
iss		pacitance	-	\/	25 \/ \/ = 0	N V			1700	2220	pF
oss		Capacitance			V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz				400	520	pF
rss		Transfer Capacitanc	e	1 1.					185	245	pF
	-	racteristics	_	1						1	
(on)		Delay Time		V _{DD} =	= 100 V, I _D = 32	2 A,			25	60	ns
		Rise Time	_	R _G =	25 Ω				270	550	ns
(off)		Delay Time					(Note 4)		245	500	ns
		Fall Time					(11010 4)		210	430	ns
g		te Charge			V _{DS} = 160 V, I _D = 32 A,				82.5	110	nC
gs		urce Charge		V _{GS} =	= 10 V		(Note 4)		10.5		nC
gd	Gate-Dra	ain Charge					(NOLE 4)		44.5		nC
rain-S	1	Diode Character				ings			I	1	
		m Continuous Drain-S								32	A
	Maximu	n Pulsed Drain-Sour								128	A
М			Voltage	V _{GS} =	= 0 V, I _S = 32 A					1.5	V
SM SD		ource Diode Forward	U						265		ns
SD	Reverse	Recovery Time			= 0 V, I _S = 32 A	۸,					-
S SM 'SD r Q _{rr}	Reverse				= 0 V, I _S = 32 A It = 100 A/μs	λ,			2.73		μC













FQA32N20C Rev. C2

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